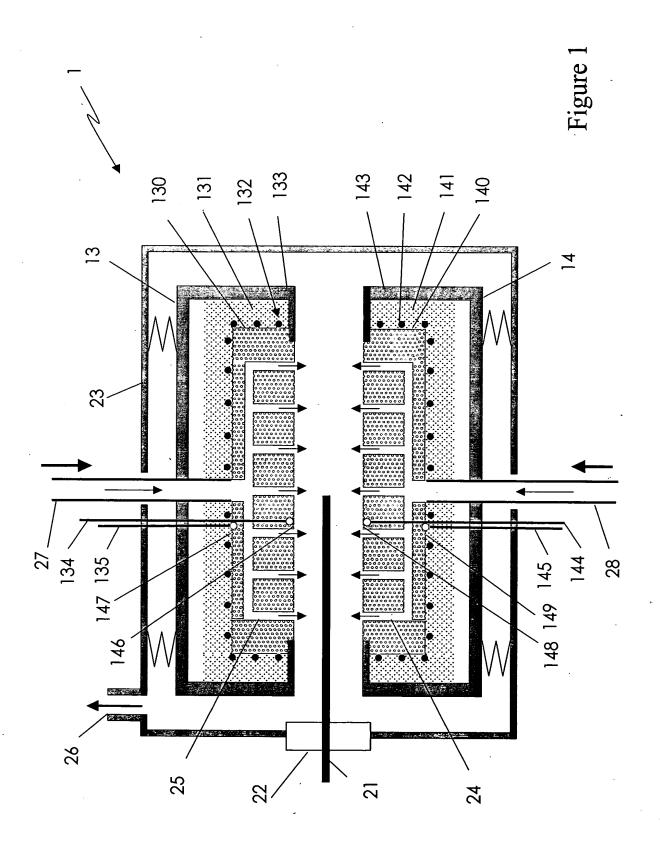
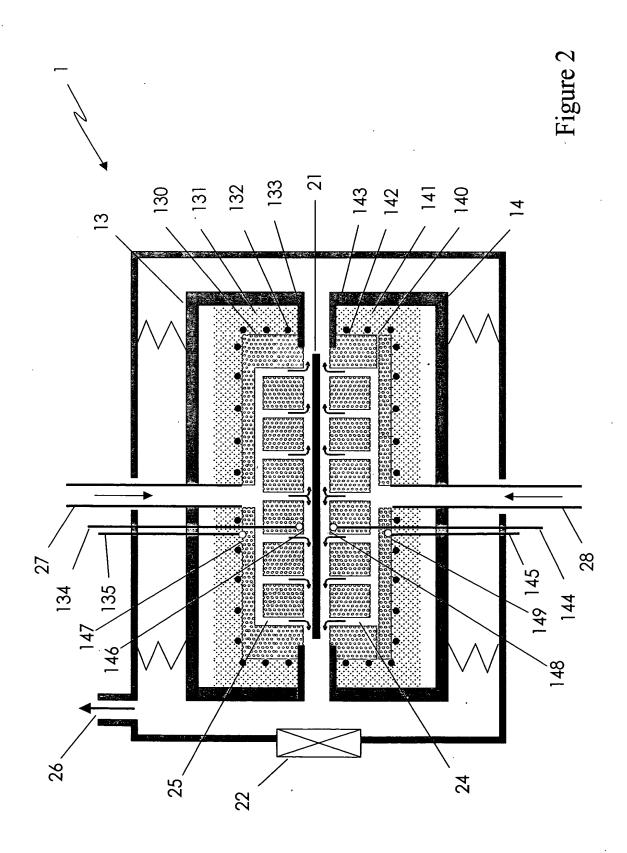
METHOD FOR HEAT TREATMENT OF SUBSTRATES Granneman et al. Appl. No.: Unknown Atty Docket: ASMINT.057AUS

Appl. No.: Unknown

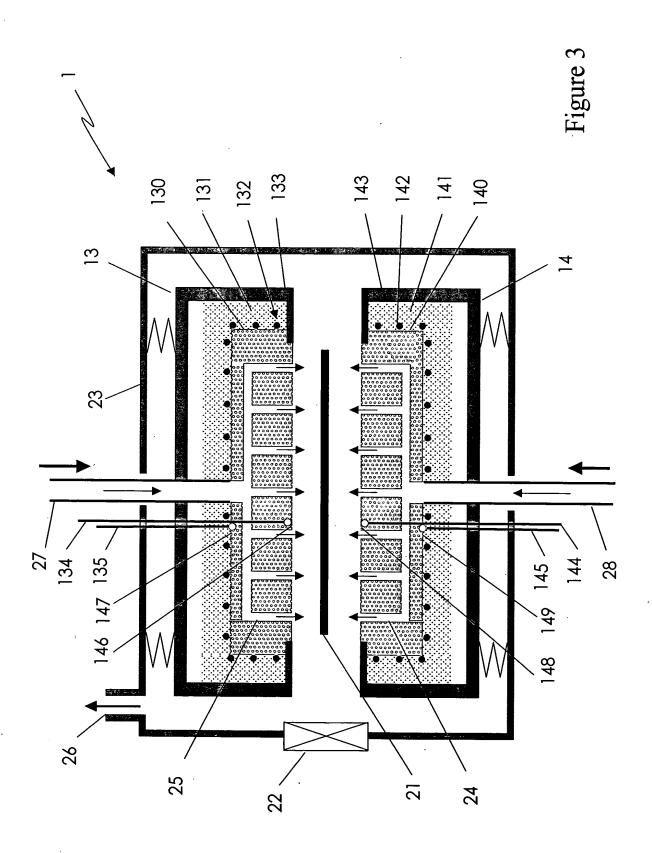


Appl. No.: Unknown



METHOD FOR HEAT TREATMENT OF SUBSTRATES Granneman et al. Appl. No.: Unknown Atty Docket: ASMINT.057AUS

Appl. No.: Unknown



METHOD FOR HEAT TREATMENT OF SUBSTRATES
Granneman et al.

Appl. No.: Unknown Atty Docket: ASMINT.057AUS

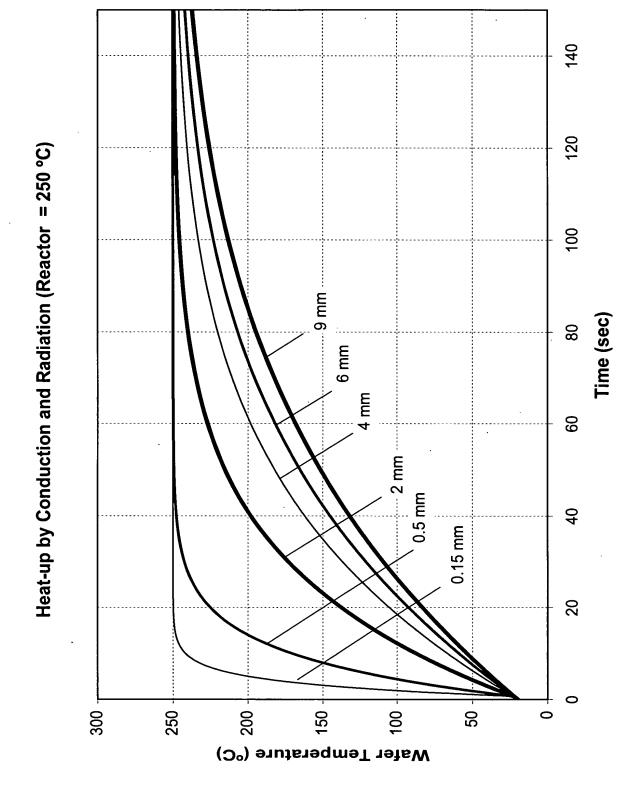


Figure 4

METHOD FOR HEAT TREATMENT OF SUBSTRATES
Granneman et al.

Appl. No.: Unknown Atty Docke

Atty Docket: ASMINT.057AUS

Heat-up by Conduction and Radiation (Reactor = 450 °C) 9 mm 6 mm 4 mm 2 mm 0.5 mm (°C) Wafer temperature

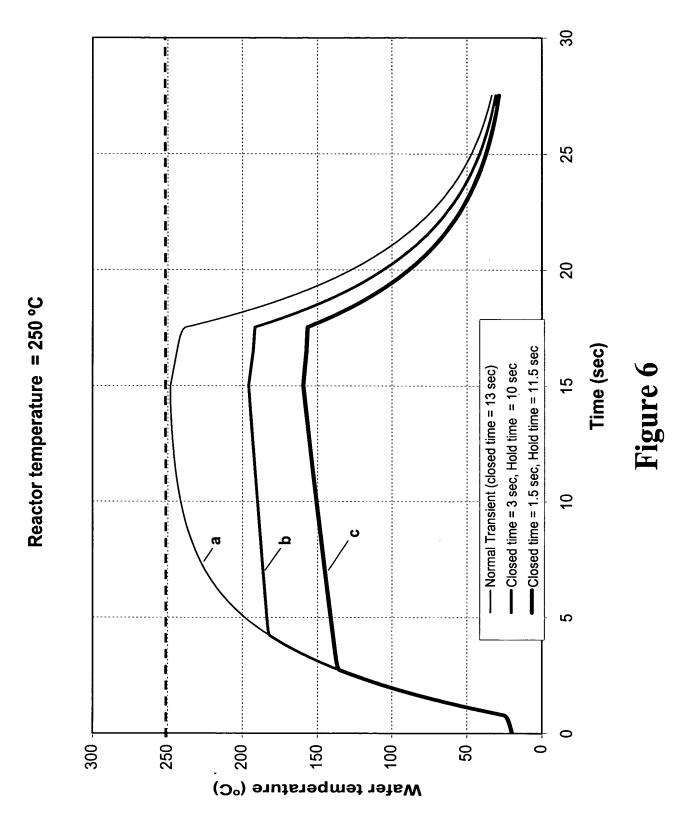
Figure 5

METHOD FOR HEAT TREATMENT OF SUBSTRATES

Grænnemæn et al.

Appl. No.: Unknown

Atty Docket: ASMINT.057AUS



Atty Docket: ASMINT.057AUS Appl. No.: Unknown

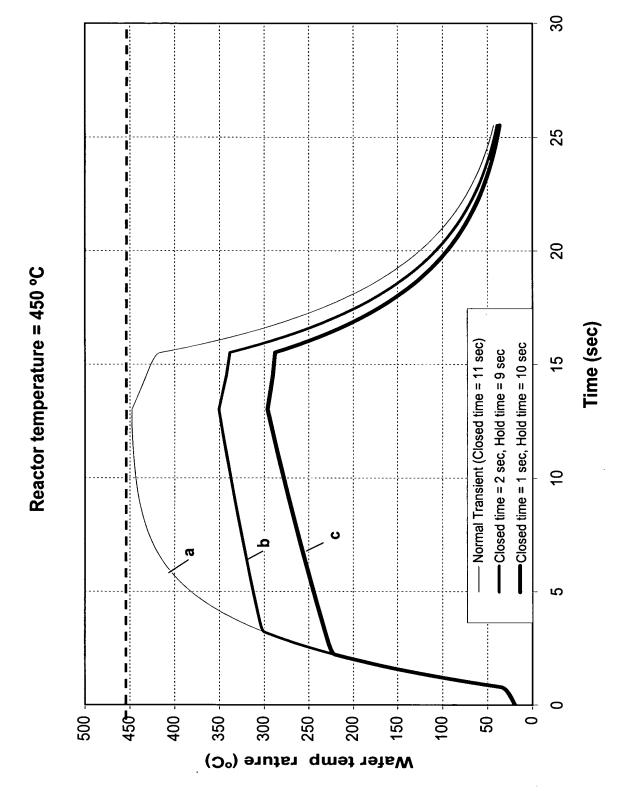


Figure 7

Appl. No.: Unknown

Granneman et al. Atty Docket: ASMINT.057AUS

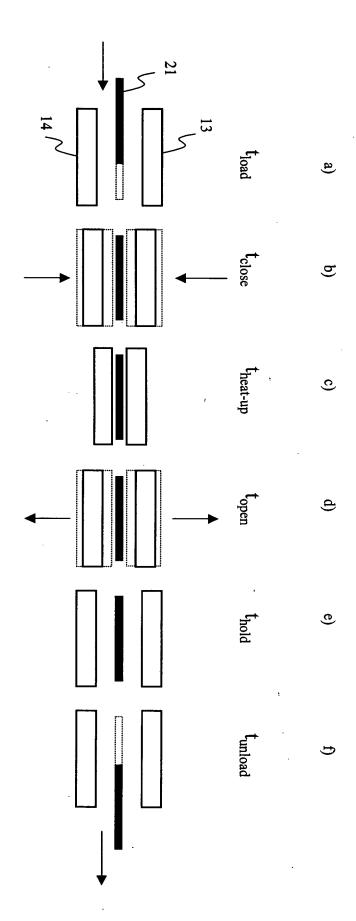


Figure 8

METHOD FOR HEAT TREATMENT OF SUBSTRATES
Granneman et al.
Appl. No.: Unknown Atty Docket: ASMINT.057AUS Appl. No.: Unknown

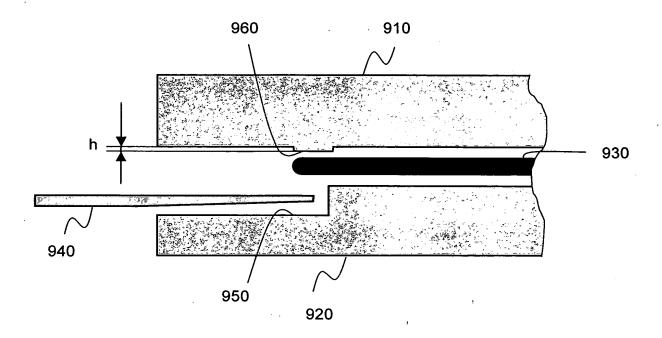


Figure 9